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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/519,408 03/03/2000		Takao Nakamura	3905	7245	
21553 7590 08/12/2002			EXAMINER		
FASSE PATENT ATTORNEYS, P.A.			LOUIE, WAI SING		
P.O. BOX 726 HAMPDEN, ME 04444-0726					
			ART UNIT	PAPER NUMBER	
			2814		
			DATE MAILED: 08/12/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.

· · · · · ·		Application N	0.	Applicant(s)	
,		09/519,408		NAKAMURA ET AL.	
	Office Action Summary	Examiner		Art Unit	
		 Wai-Sing Lou	ie	2814	
	The MAILING DATE of this communication ap	ppears on the co	ver sheet with the	correspondence addr	ess
ried for	Donly				
THE W - Extens after S - If the p - If NO - Failure - Any re earned	PRTENED STATUTORY PERIOD FOR REPLAILING DATE OF THIS COMMUNICATION is sions of time may be available under the provisions of 37 CFR 1 (ix (6) MONTHS from the mailing date of this communication. Deriod for reply specified above is less than thirty (30) days, a reperiod for reply is specified above, the maximum statutory period to reply within the set or extended period for reply will, by status ply received by the Office later than three months after the mailed patent term adjustment. See 37 CFR 1.704(b).		minimum of thirty (30) do	imely filed ays will be considered timely. The mailing date of this com FD (35 U.S.C. § 133).	munication.
tatus	Responsive to communication(s) filed on 28	8 June 2002 .			
1)⊠ 2a)□	This setion is EINAL 2b)	This action is no	n-final.		
3)	Since this application is in condition for allocolosed in accordance with the practice undo on of Claims	wance except fo er <i>Ex parte Qua</i>	or formal matters, yle, 1935 C.D. 11	prosecution as to the , 453 O.G. 213.	merits is
4)[⊠	Claim(s) 16-22 is/are pending in the applica	ation.			
•	4a) Of the above claim(s) is/are withd	lrawn from cons	ideration.		
	Claim(s) is/are allowed.				
•	Claim(s) 16-22 is/are rejected.				
7)[]	Claim(s) is/are objected to.				
8)□	Claim(s) are subject to restriction and	d/or election red	uirement.		
Applicat	ion Papers				
9)[The specification is objected to by the Exam	niner.	by tho F	vaminer	
10)[The drawing(s) filed on is/are: a) ac	ccepted or b) 0	bjected to by the L	See 37 CFR 1.85(a).	
	Applicant may not request that any objection to	o the drawing(s) o	e neid in abeyance	proved by the Examin	er.
11)	The proposed drawing correction filed on	is: a) Lap	oo action	,p. 6 * 6 * 2 * 2 * 2 * 2 * 2 * 2 * 2 * 2 *	
	If approved, corrected drawings are required in	n reply to this Oil	ce action.		
	The oath or declaration is objected to by the	e Examiner.			
Priority	under 35 U.S.C. §§ 119 and 120		1 25 II S C 8 11	19(a)-(d) or (f)	
	Acknowledgment is made of a claim for for	reign priority und	ier 35 U.S.C. 9 11	(a) (a) o. (.).	
а	ı)⊠ All b)□ Some * c)□ None of:				
	1.⊠ Certified copies of the priority docum	nents have beer	received.	ication No	
	2. Certified copies of the priority docum	nents have beer	received in Appi	cation No	Stage
•	Copies of the certified copies of the application from the International See the attached detailed Office action for a	a list of the certif	ied copies not rec	eived.	
44)	See the attached detailed Office action for don Acknowledgment is made of a claim for don	nestic priority ur	ider 35 U.S.C. § 1	19(e) (to a provision	al application)
	a) The translation of the foreign languag Acknowledgment is made of a claim for dor	e nrovisional ab	Diication nas neei	TIECCIVCU.	
Attachm					(a/a)
1) 🔀 No	otice of References Cited (PTO-892) otice of Draftsperson's Patent Drawing Review (PTO-94 formation Disclosure Statement(s) (PTO-1449) Paper N	.8) lo(s) <u>21</u> .	4) Interview Sur 5) Notice of Info 6) Other:	nmary (PTO-413) Paper N rmal Patent Application (P	o(s) · TO-152)
	nd Trademark Office			Part	of Paper No. 22

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DETAILED ACTION

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter, which the applicant regards as his invention.

- 1. Claim 5 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
 - In claim 16, 18, and 20-22, the term "n-type transparent conductor film" is an
 inappropriate term and is not supported by the specification. For the purpose of
 examination, "transparent conductor film" is assumed.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 16, 18-20, and 22 (in so far as they are understood) are rejected under 35 U.S.C. 103(a) as being unpatentable over Ishibashi et al. (US 5,617,446) in view of Kazuyoshi et al. (JP 06-318406).

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With regard to claim 16, Ishibashi et al. disclose a semiconductor light-emitting device (col. 3, line 8 to col. 9, line 58 and fig. 2) comprising:

- A substrate 1 provided with an n-type lower electrode on the back surface;
- A light-emitting layer 6 provided on the substrate 1;
- A p-type semiconductor layer 12 provided on the light-emitting layer 6, where the p-type semiconductor layer 12 is a ZnTe-based semiconductor layer;
- An upper electrode 13 and 14 provided on the p-type semiconductor layer 12, where the upper electrode includes an Au thin film positioned in contact with the p-type semiconductor layer 12, but Ishibashi et al. do not disclose a transparent thin film formed on the Au thin film. However, Kazuyoshi et al. disclose a transparent conductive layer, which is made of In and Zn compound (Kazuyoshi [0008]). Kazuyoshi et al. teach that this compound is transparent, conductive, resistant to heat and high humidity, and is suitable to be a transparent electrode (Kazuyoshi [0018]). Hence, it would have been obvious at the time the invention was made to provide Kazuyoshi's transparent conductor layer on Ishibashi's Au thin film to seal the air and humidity from the Au layer.

With regard to claim 18, Ishibashi et al. modified by Kazuyoshi et al. in claim 2 above would have an In_2O_3/ZnO layer on top of the Au thin layer and Kazuyoshi et al. disclose the In₂O₃ is 90% by weight (page 3, paragraph [0014]).

With regard to claim 19, Ishibashi et al. modified by Kazuyoshi et al. would have an $In_2O_{3-}10wt.\%$ ZnO layer, but they do not disclose the $In_2O_{3-}10wt.\%$ ZnO layer is formed by laser

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ablation. However, this is a process limitation, which carries no patentable weight in a claim drawn to a device.

With regard to claim 20, Ishibashi et al., modified by Woodard et al. in claim 17 above, disclose an Au thin film has a thickness of 0.6 to 30 Å and Ishibashi et al., modified by Kazuyoshi et al. in claim 18 above, disclose an In_2O_3 -10 wt.% ZnO layer. Kazuyoshi et al. disclose the thickness is 10 to 800 nm (Kazuyoshi [0017]).

With regard to claim 22, Ishibashi et al. modified by Kazuyoshi et al. would have an $In_2O_{3-}10$ wt.% ZnO layer. Kazuyoshi et al. disclose the transparent conductor film is form @20°C (Kazuyoshi [0066]).

Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over Ishibashi et al. (US 5,617,446) modified by Kazuyoshi et al. (JP 06-318406 as applied to claim 16 above, and further in view of Woodard et al. (US 6,255,003).

With regard to claim 17, Ishibashi et al. do not disclose the thickness of the Au thin film. However, Woodard et al. teach that Au has an effective thickness as thin as on tenth of a full 3 Å thick monolayer (Woodard col. 5, lines 20-24). Woodard et al. disclose the common thickness of a transparent Au thin film is about 1 to 10 Å (Woodard col. 5, lines 24-28) and film 104 in Woodard's device is 0.6 to 30 Å (Woodard col. 5, line 26 and fig. 1). Therefore, it would have been obvious to one with ordinary skill in the art to provide an Au thin film of less than 3 nm thick in order to provide a conductive, transparent film.

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Claim 21 is rejected under 35 U.S.C. 103(a) as being unpatentable over Ishibashi et al. (US 5,617,446) modified by Kazuyoshi et al. (JP 06-318406) as applied to claim 16 above, and further in view of Lawrence et al. (US 4,495,514).

With regard to claim 21, Ishibashi et al. modified by Kazuyoshi et al. disclose a multi layer structure upper electrode, but do not disclose the lower layer having a flattened surface and the upper layer having an uneven surface. However, Lawrence et al. disclose an electrode having a thin gold layer, which is a flattened layer, and an uneven upper transparent layer (Lawrence col. 6, lines 44-57). Lawrence et al. teach the thin gold layer could reduce the contact resistance at the electrode-semiconductor interface (Lawrence col. 6, lines 47-50). Therefore, it would have been obvious to one with ordinary skill in the art to provide a thin gold flattened layer and an uneven transparent electrode in order to reduce the contact resistance at the electrode-semiconductor interface.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (703) 305-0474. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Douglas A. Wille
Patent Examiner

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August 7, 2002